

Form PTO 1449  
(Modified)U.S. DEPARTMENT OF COMMERCE  
PATENT AND TRADEMARK OFFICE

ATTY DOCKET NO.

210136US99

SERIAL NO.

09/901,109

APPLICANT

Ravindranath DROOPAD, et al.

FILING DATE

July 10, 2001

GROUP

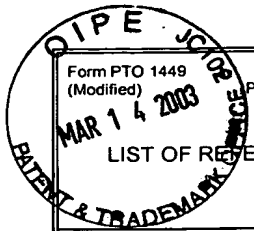
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LIST OF REFERENCES CITED BY APPLICANT

MAR 14 2003

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
BWB	AA	3,802,967	04/09/74	Ladany et al.			
	AB	4,174,422	11/13/79	Matthews et al.			
	AC	4,404,265	09/13/83	Manasevit			
	AD	4,482,906	11/13/84	Hovel et al.			
	AE	4,523,211	06/11/85	Morimoto et al.			
	AF	4,661,176	04/28/87	Manasevit			
	AG	4,793,872	12/27/88	Meunier et al.			
	AH	4,846,926	07/11/89	Kay et al.			
	AJ	4,855,249	08/08/89	Akasaki et al.			
	AI	4,891,091	01/02/90	Shastri			
	AK	4,912,087	03/27/90	Aslam et al.			
	AL	4,928,154	05/22/90	Umeno et al.			
	AM	4,963,949	10/16/90	Wanlass et al.			
	AN	5,141,894	08/25/92	Bisaro et al.			
	AO	5,159,413	10/27/92	Calviello et al.			
	AP	5,173,474	12/22/92	Connell et al.			
	AQ	5,221,367	06/22/93	Chisholm et al.			
	AR	5,225,031	07/06/93	McKee et al.			
	AS	5,358,925	10/25/94	Neville Connell et al.			
	AT	5,393,352	02/28/95	Summerfelt			
	AU	5,418,216	05/23/95	Fork			
	AV	5,450,812	09/19/95	McKee et al.			
	AW	5,478,653	12/26/95	Guenzer			
	AX	5,482,003	01/09/96	McKee et al.			
	AY	5,514,484	05/07/96	Nashimoto			
	AZ	5,556,463	09/17/96	Guenzer			
	BA	5,588,995	12/31/96	Sheldon			
	BB	5,670,798	09/23/97	Schetzina			
	BC	5,733,641	03/31/98	Fork et al.			
	BD	5,735,949	04/07/98	Mantl et al.			
	BE	5,741,724	04/21/98	Ramdani et al.			
	BF	5,810,923	09/22/98	Yano et al.			
	BG	5,830,270	11/03/98	McKee et al.			
	BH	5,912,068	06/15/99	Jia			
	BI	6,020,222	02/01/00	Wollesen			
	BJ	6,045,626	04/04/00	Yano et al.			
	BK	6,064,078	05/16/00	Northrup et al.			
	BL	6,064,092	05/16/00	Park			
	BM	6,096,584	08/01/00	Ellis-Monaghan et al.			
	BN	6,103,008	08/15/00	McKee et al.			
	BO	6,136,666	10/24/00	So			
	BP	6,174,755	01/16/01	Manning			
	BQ	6,180,486	01/30/01	Leobandung et al.			

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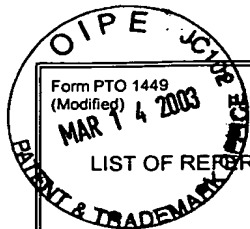
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## U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
BMB	CA	3,766,370	10/16/73	Walther			
	CB	4,006,989	02/08/77	Andringa			
	CC	4,284,329	08/18/81	Smith et al.			
	CD	4,777,613	10/11/98	Shahan et al.			
	CE	4,802,182	01/31/89	Thornton et al.			
	CF	4,882,300	11/21/89	Inoue et al.			
	CG	4,896,194	01/23/90	Suzuki			
	CH	4,999,842	03/12/91	Huang et al.			
	CI	5,081,062	01/14/92	Vasudev et al.			
	CJ	5,155,658	10/13/92	Inam et al.			
	CK	5,248,564	09/28/93	Ramesh			
	CL	5,260,394	11/09/93	Tazaki et al.			
	CM	5,270,298	12/14/93	Ramesh			
	CN	5,286,985	02/15/94	Taddiken			
	CO	5,310,707	05/10/94	Oishi et al.			
	CP	5,326,721	07/05/94	Summerfelt			
	CQ	5,404,581	04/04/95	Honjo			
	CR	5,418,389	05/23/95	Watanabe			
	CS	5,436,759	07/25/95	Dijail et al.			
	CT	5,576,879	11/19/96	Nashimoto			
	CU	5,606,184	02/25/97	Abrokwah, et al.			
	CV	5,640,267	06/17/97	May et al.			
	CW	5,674,366	10/07/97	Hayashi et al.			
	CX	5,729,641	03/17/98	Chandonnet et al.			
	CY	5,790,583	08/04/98	Ho			
	CZ	5,825,799	10/20/98	Ho et al.			
	DA	5,857,049	01/05/99	Beranek et al.			
	DB	5,874,860	02/23/99	Brunel et al.			
	DC	5,926,496	07/20/99	Ho et al.			
	DD	5,937,285	08/10/99	Abrokwah, et al.			
	DE	5,981,400	11/09/99	Lo			
	DF	5,990,495	11/23/99	Ohba			
	DG	6,002,375	12/14/99	Corman et al.			
	DH	6,008,762	12/28/99	Nghiem			
	DI	6,055,179	04/25/00	Koganei et al.			
	DJ	6,107,653	08/22/00	Fitzgerald			
	DK	6,113,690	09/05/00	Yu et al.			
	DL	6,114,996	09/05/00	Nghiem			
	DM	6,121,642	09/19/00	Newns			
	DN	6,128,178	10/03/00	Newns			
	DO	6,143,072	11/07/00	McKee et al.			
	DP	6,184,144	02/06/01	Lo			
	DQ	6,222,654	04/24/01	Frigo			



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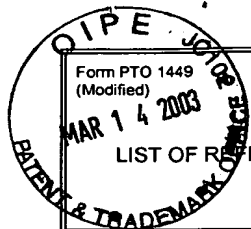
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U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
BWB	EA	4,484,332	11/20/84	Hawrylo			
	EB	4,815,084	03/21/89	Scifres et al.			
	EC	4,876,219	10/24/89	Eshita et al.			
	ED	4,963,508	10/16/90	Umeno et al.			
	EE	5,060,031	10/22/91	Abrokwah, et al.			
	EF	5,063,166	11/05/91	Mooney et al.			
	EG	5,116,461	05/26/92	Lebby et al.			
	EH	5,127,067	06/30/92	Delcoco et al.			
	EI	5,144,409	09/01/92	Ma			
	EJ	5,293,050	03/08/94	Chapple-Sokol et al			
	EK	5,356,831	10/18/94	Calviello et al.			
	EL	5,391,515	02/21/95	Kao et al.			
	EM	5,442,191	08/15/95	Ma			
	EN	5,444,016	08/22/95	Abrokwah, et al.			
	EO	5,480,829	01/02/96	Abrokwah, et al.			
	EP	5,528,414	06/18/96	Oakley			
	EQ	5,614,739	03/25/97	Abrokwah et al.			
	ER	5,729,394	03/17/98	Sevier et al.			
	ES	5,731,220	03/24/98	Tsu et al.			
	ET	5,764,676	06/09/98	Paoli et al.			
	EU	5,777,762	07/07/98	Yamamoto			
	EV	5,778,018	07/07/98	Yoshikawa et al.			
	EW	5,778,116	07/07/98	Tomich			
	EX	5,801,105	09/01/98	Yano et al.			
	EY	5,828,080	10/27/98	Yano et al.			
	EZ	5,858,814	01/12/99	Goossen et al.			
	FA	5,861,966	01/19/99	Ortel			
	FB	5,883,996	03/16/99	Knapp et al.			
	FC	5,995,359	11/30/99	Klee et al.			
	FD	6,058,131	05/02/00	Pan			
	FE	6,137,603	10/24/00	Henmi			
	FF	6,146,906	11/14/00	Inoue et al.			
	FG	6,173,474	01/16/01	Conrad			
	FH	6,180,252	01/30/01	Farrell et al.			
	FI	4,242,595	12/30/0	Lehovec			
	FJ	4,398,342	08/16/83	Pitt et al.			
	FK	4,424,589	01/03/84	Thomas et al.			
	FL	4,876,208	10/24/89	Gustafson et al.			
	FM	4,482,422	11/84	McGinn et al.			
	FN	4,667,088	05/19/87	Kramer			
	FO	4,772,929	09/20/88	Manchester et al.			
	FP	4,841,775	06/27/89	Ikeda et al.			
	FQ	4,845,044	07/04/89	Ariyoshi et al.			

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EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
BWB	GA	4,868,376	09/19/89	Lessin et al.			
	GB	4,885,376	12/05/89	Verkade			
	GC	4,888,202	12/89	Murakami et al.			
	GD	4,891,091	12/90	Wanlass et al.			
	GE	5,051,790	09/24/91	Hammer			
	GF	5,055,445	10/08/91	Belt et al.			
	GG	5,081,519	11/14/92	Nishimura et al.			
	GH	5,143,854	09/01/92	Pirung et al.			
	GI	5,185,589	02/09/93	Krishnaswamy et al.			
	GJ	5,191,625	03/02/93	Gustavsson			
	GK	5,194,397	03/16/93	Cook et al.			
	GL	5,208,182	05/04/93	Narayan et al.			
	GM	5,216,729	06/01/93	Berger et al.			
	GN	5,314,547	05/24/94	Heremans et al.			
	GO	5,352,926	10/04/94	Andrews			
	GP	5,356,509	10/18/94	Terranova et al.			
	GQ	5,371,734	12/06/94	Fischer			
	GR	5,372,992	12/94	Itozaki et al.			
	GS	5,405,802	04/11/95	Yamagata et al.			
	GT	5,442,561	08/15/95	Yoshizawa et al.			
	GU	5,453,727	09/26/95	Shibasaki et al.			
	GV	5,466,631	11/14/95	Ichikawa et al.			
	GW	5,473,047	12/05/95	Shi			
	GX	5,473,171	12/95	Summerfelt			
	GY	5,479,033	12/26/95	Baca et al.			
	GZ	5,486,406	01/23/96	Shi			
	HA	5,491,461	02/13/96	Partin et al.			
	HB	5,492,859	02/20/96	Sakaguchi et al.			
	HC	5,494,711	02/27/96	Takeda et al.			
	HD	5,504,035	04/02/96	Rostoker et al.			
	HE	5,504,183	04/02/96	Shi			
	HF	5,511,238	04/23/96	Bayraktaroglu			
	HG	5,512,773	04/96	Wolf et al.			
	HH	5,515,047	05/07/96	Yamakido et al.			
	HI	5,515,810	05/14/96	Yamashita et al.			
	HJ	5,519,235	05/96	Ramesh			
	HK	5,549,977	08/96	Jin et al.			
	HL	5,551,238	09/03/96	Prueitt			
	HM	5,552,547	09/03/96	Shi			
	HN	5,589,284	12/31/96	Summerfelt et al.			
	HO	5,602,418	02/11/97	Imai et al.			
	HP	5,633,724	05/27/97	King et al.			

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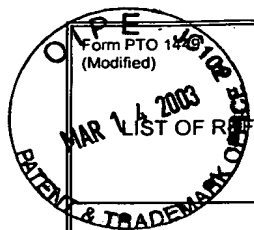
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## U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
AMB	IA	5,650,646	07/22/97	Summerfelt			
	IB	5,656,382	08/12/97	Nashimoto			
	IC	5,659,180	08/19/97	Shen et al.			
	ID	5,661,112	08/26/97	Hatta et al.			
	IE	5,679,965	11/95	Schetzina			
	IF	5,725,641	03/10/98	MacLeod			
	IG	5,745,631	04/28/98	Reinker			
	IH	5,776,621	07/07/98	Nashimoto			
	II	5,777,350	07/07/98	Nakamura et al.			
	IJ	5,789,845	08/04/98	Wadaka et al.			
	IK	5,792,569	08/11/98	Sun et al.			
	IL	5,792,679	08/11/98	Nakato			
	IM	5,796,648	08/18/98	Kawakubo et al.			
	IN	5,801,072	09/01/98	Barber			
	IO	5,812,272	09/22/98	King et al.			
	IP	5,814,583	09/98	Itozaki et al.			
	IQ	5,825,055	10/20/98	Summerfelt			
	IR	5,827,755	10/27/98	Yonchara et al.			
	IS	5,833,603	11/10/98	Kovacs et al.			
	IT	5,838,035	11/17/98	Ramesh			
	IU	5,844,260	12/01/98	Ohori			
	IV	5,846,846	12/08/98	Suh et al.			
	IW	5,863,326	01/26/99	Nause et al.			
	IX	5,872,493	02/16/99	Ella			
	IY	5,879,956	03/99	Seon et al.			
	IZ	5,880,452	03/09/99	Plesko			
	JA	5,883,564	03/16/99	Partin			
	JB	5,907,792	05/25/99	Droopad et al.			
	JC	5,937,274	08/10/99	Kondow et al.			
	JD	5,948,161	09/07/99	Kizuki			
	JE	5,959,879	09/28/99	Koo			
	JF	5,966,323	10/99	Chen et al.			
	JG	5,987,011	11/16/99	Toh			
	JH	6,022,140	02/08/00	Fraden et al.			
	JI	6,022,410	02/08/00	Yu et al.			
	JJ	6,023,082	02/08/00	McKee et al.			
	JK	6,028,853	02/22/00	Haartsen			
	JL	6,049,702	04/11/00	Tham et al.			
	JM	6,078,717	06/20/00	Nashimoto et al			
	JN	6,088,216	07/00	Laibowitz et al.			
	JO	6,090,659	07/00	Laibowitz et al.			
	JP	6,107,721	08/22/00	Lakin			
	JQ	6,153,010	11/28/00	Kiyoku et al			



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BWB	KA	6,153,454	11/28/00	Krivokapic			
	KB	6,191,011	02/01	Gilboa et al			
	KC	6,204,737	03/20/01	Ella			
	KD	6,224,669	05/01/01	Yi et al.			
	KE	6,225,051	05/01/01	Sugiyama et al.			
	KF	6,241,821	06/05/01	Yu et al.			
	KG	6,265,749	07/24/01	Gardner et al.			
	KH	6,313,486	11/01	Kencke et al.			
	KI	6,316,832	11/13/01	Tsuzuki et al.			
	KJ	2002/0008234	01/02	Emrick			
	KK	3,670,213	06/13/72	Nakawaga et al.			
	KL	4,756,007	07/05/88	Qureshi et al.			
	KM	4,773,063	09/20/88	Hunsperger et al.			
	KN	5,394,489	02/28/95	Koch			
	KO	5,406,202	04/11/95	Mehrgardt et al.			
	KP	5,528,067	06/18/96	Farb et al.			
	KQ	5,572,052	11/05/96	Kashihara et al.			
	KR	5,767,543	06/16/98	Ooms et al.			
	KS	6,175,497	01/16/01	Tseng et al.			
	KT	6,197,503	03/06/01	Vo-Dinh et al.			
	KU	6,248,459	06/19/01	Wang et al.			
	KV	6,252,261	06/26/01	Usui et al.			
	KW	6,255,198	07/03/01	Linthicum et al.			
	KX	6,268,269	07/31/01	Lee et al.			
	KY	6,291,319	09/18/01	Yu et al.			
	KZ	6,316,785	11/13/01	Nunoue et al.			
	LA	6,343,171	01/29/02	Yoshimura et al.			
	LB	4,965,649	10/23/90	Zanio et al.			
	LC	6,253,649	05/01	Kawahara et al.			
	LD	6,211,096	04/01	Allman et al.			
	LE	6,239,449	05/29/01	Fafard et al.			
	LF	2001/0013313	08/16/01	Droopad et al.			
	LG	6,184,044	02/06/01	Sone et al.			
	LH	6,011,646	01/04/00	Mirkarimi et al.			
	LI	5,227,196	07/13/93	Itoh			
	LJ	6,150,239	11/21/00	Goesele et al.			
	LK	5,441,577	08/15/95	Sasaki et al.			
	LL	4,459,325	07/10/84	Nozawa et al.			
	LM	4,392,297	07/12/83	Little			
	LN	4,289,920	09/15/81	Hovel			
	LO	5,281,834	01/25/94	Cambou et al.			
	LP	4,901,133	02/13/90	Curran et al.			
	LQ	5,514,904	05/07/96	Onga et al.			

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BNB	MA	5,553,089	09/03/96	Seki et al.			
	MB	5,528,057	06/18/96	Yanagase et al.			
	MC	6,229,159	05/08/01	Suzuki			
	MD	4,748,485	05/31/88	Vasudev			
	ME	4,984,043	01/08/91	Vinal			
	MF	5,754,319	05/19/98	Van De Voorde et al.			
	MG	6,108,125	08/22/00	Yano			
	MH	5,073,981	12/17/91	Giles et al.			
	MI	5,140,651	08/18/92	Soref et al.			
	MJ	5,610,744	03/11/97	Ho et al.			
	MK	6,362,017	03/26/02	Manabe et al.			
	ML	6,242,686	06/05/01	Kishimoto et al.			
	MM	5,689,123	11/18/97	Major et al.			
	MN	5,670,800	09/23/97	Nakao et al.			
	MO	5,067,809	11/26/91	Tsubota			
	MP	5,596,205	01/21/97	Reedy et al.			
	MQ	6,175,555	01/16/01	Hoole			
	MR	5,357,122	10/18/94	Okubora et al.			
	MS	4,084,130	04/11/78	Holton			
	MT	6,093,302	07/25/00	Montgomery			
	MU	6,372,813	04/16/02	Johnson et al.			
	MV	5,608,046	03/04/97	Cook et al.			
	MW	5,955,591	09/21/99	Imbach et al.			
	MX	6,022,963	02/08/00	McGall et al.			
	MY	6,083,697	07/04/00	Beecher et al.			
	MZ	5,063,081	11/05/91	Cozzette et al.			
	NA	5,479,317	12/26/95	Ramesh			
	NB	5,306,649	04/26/94	Hebert			
	NC	5,962,069	10/05/99	Schindler et al.			
	ND	5,541,422	07/30/96	Wolf et al.			
	NE	5,873,977	02/23/99	Desu et al.			
	NF	5,538,941	07/23/96	Findikoglu et al.			
	NG	6,046,464	04/04/00	Schetzina			
	NH	6,235,145	05/22/01	Li et al.			
	NI	5,610,744	03/11/97	Ho et al.			
	NJ	5,280,013	01/18/94	Newman et al.			
	NK	6,348,373 B1	02/19/02	Ma et al.			
	NL	6,339,664 B1	01/15/02	Farjady et al.			
	NM	4,439,014	03/27/84	Stacy et al.			
	NN	4,889,402	12/26/89	Reinhart			
	NO	5,963,291	10/05/99	Wu et al.			
	NP	6,011,641	01/04/00	Shin et al.			
	NQ	6,340,788 B1	01/22/02	King et al.			

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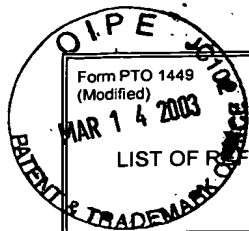
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BWB	OA	5,807,440	09/15/98	Kubota et al.			
	OB	4,681,982	07/21/87	Yoshida			
	OC	4,629,821	12/16/86	Bronstein-Bonte et al.			
	OD	4,452,720	06/05/84	Harada et al.			
	OE	3,935,031	01/27/76	Adler			
	OF	5,760,426	06/02/98	Marx et al.			
	OG	5,053,835	10/01/91	Horikawa et al.			
	OH	6,326,645 B1	12/04/01	Kadota			
	OI	5,770,887	06/23/98	Tadatomo et al.			
	OJ	6,372,356 B1	04/16/02	Thornton et al.			
	OK	4,774,205	09/27/88	Choi et al.			
	OL	6,359,330 B1	03/19/02	Goudard			
	OM	5,312,765	05/17/94	Kanber			
	ON	5,734,672	03/31/98	McMinn et al.			
	OO	6,367,699 B2	04/09/02	Ackley			
	OP	5,530,235	06/25/96	Stefik et al.			
	OQ	5,623,552	04/22/97	Lane			
	OR	5,481,102	01/02/96	Hazelrigg, Jr.			
	OS	6,134,114	10/17/00	Ungermann et al.			
	OT	5,984,190	11/16/99	Nevill			
	OU	5,789,733	08/04/98	Jachimowicz et al.			
	OV	5,753,300	05/19/98	Wessels et al.			
	OW	6,208,453	03/27/01	Wessels et al.			
	OX	5,886,867	03/23/99	Chivukula et al.			
	OY	5,028,976	07/02/91	Ozaki et al.			
	OZ	5,869,845	02/09/99	Vander Wagt et al.			
	PA	5,596,214	01/21/97	Endo			
	PB	6,391,674 B2	05/21/02	Ziegler			
	PC	6,275,122 B1	08/14/01	Speidell et al.			
	PD	6,238,946 B1	05/29/01	Ziegler			
	PE	6,210,988 B1	04/03/01	Howe et al.			
	PF	6,392,257	05/21/02	Ramdani et al.			
	PG	4,442,590	04/17/84	Stockton et al.			
	PH	5,603,764	02/18/97	Matsuda et al.			
	PI	6,087,681	06/11/00	Shakuda			
	PJ	5,132,648	07/21/92	Trinh et al.			
	PK	6,427,066	07/30/02	Grube			
	PL	2002/0072245	06/13/02	Ooms et al.			
	PM	6,278,138 B1	08/21/01	Suzuki			
	PN	5,888,296	03/30/99	Ooms et al.			
	PO	5,198,269	03/30/93	Swartz et al.			
	PP	2002/0030246	03/14/02	Eisenbeiser et al.			
	PQ	2002/0047143	04/25/02	Ramdani et al.			

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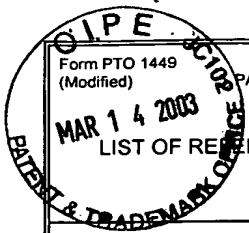
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BWB	QA	5,776,359	07/07/98	Schultz et al.			
	QB	5,569,953	10/29/96	Kikkawa et al.			
	QC	5,834,362	11/10/98	Miyagaki et al.			
	QD	6,248,621 B1	06/19/01	Wilk et al.			
	QE	5,266,355	11/30/93	Wernberg et al.			
	QF	6,277,436 B1	08/21/01	Stauf et al.			
	QG	6,039,803	03/21/00	Fitzgerald et al.			
	QH	5,619,051	04/08/97	Endo			
	QI	5,420,102	05/30/95	Harshavardhan et al.			
	QJ	5,210,763	05/11/93	Lewis et al.			
	QK	5,103,494	04/07/92	Mozer			
	QL	4,594,000	06/10/86	Falk et al.			
	QM	4,297,656	10/27/81	Pan			
	QN	5,244,818	09/14/93	Jokers et al.			
	QO	6,048,751	04/11/00	D'Asaro et al.			
	QP	5,484,664	01/16/96	Kitahara et al.			
	QQ	5,780,311	07/14/98	Beasom et al.			
	QR	6,438,281 B1	08/20/02	Tsukamoto et al.			
	QS	5,399,898	03/21/95	Rostoker			
	QT	6,271,619	08/07/01	Yamada et al.			
	QU	5,334,556	08/02/94	Guldi			
	QV	4,910,164	03/20/90	Shichijo			
	QW	4,952,420	08/28/90	Walters			
	QX	6,121,647	09/19/00	Yano et al.			
	QY	6,306,668 B1	10/23/01	McKee et al.			
	QZ	6,143,366	11/07/00	Lu			
	RA	6,410,941	06/25/02	Taylor et al.			
	RB	5,397,428	03/14/95	Stoner et al.			
	RC	6,432,546 B1	08/13/02	Ramesh et al.			
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	RE	6,338,756 B2	01/15/02	Dietze			
	RF	5,516,725	05/14/96	Chang et al.			
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	RH	5,629,534	05/13/97	Inuzuka et al.			
	RI	3,914,137	10/21/75	Huffman et al.			
	RJ	5,753,928	05/19/98	Krause			
	RK	5,977,567	11/02/99	Verdiell			
	RL	5,130,762	07/14/92	Kulick			
	RM	5,621,227	04/15/97	Joshi			
	RN	6,389,209 B1	05/14/02	Suhir			
	RO	5,163,118	11/10/92	Lorenzo et al.			
	RP	5,926,493	07/20/99	O'Brien et al.			
	RQ	5,323,023	06/21/94	Fork			

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BWB	SA	6,156,581	12/05/00	Vaudo et al.			
	SB	5,395,663	03/07/95	Tabata et al.			
	SC	4,146,297	03/27/79	Alferness et al.			
	SD	5,452,118	09/19/95	Maruska			
	SE	5,889,296	03/30/99	Imamura et al.			
	SF	6,300,615 B1	10/09/01	Shinohara et al.			
	SG	6,232,910 B1	05/15/01	Bell et al.			
	SH	5,686,741	11/11/97	Ohori et al.			
	SI	4,959,702	09/25/90	Moyer et al			
	SJ	6,100,578	08/08/00	Suzuki			
	SK	6,410,947 B1	06/25/02	Wada			
	SL	6,417,059 B2	07/09/02	Huang			
	SM	6,461,927 B1	10/08/02	Mochizuki et al.			
	SN	6,462,360 B1	10/08/02	Higgins, Jr. et al.			
	SO	5,981,976	11/09/99	Murasato			
	SP	5,981,980	11/09/99	Miyajima et al.			
	SQ	2002/0006245 A1	01/17/02	Kubota et al.			
	SR	2002/0131675 A1	09/19/02	Litvin			
	SS	6,256,426 B1	07/03/01	Duchet			
	ST	6,278,523 B1	08/21/01	Gorecki			
	SU	6,319,730 B1	11/20/01	Ramdani et al.			
	SV	6,404,027	06/11/02	Hong et al.			
	SW	6,312,819 B1	11/06/01	Jia et al.			
	SX	5,119,448	06/02/92	Schaefer et al.			
	SY	4,120,588	10/17/78	Chaum			
	SZ	5,194,917	03/16/93	Regener			
	TA	5,018,816	05/28/91	Murray et al.			
	TB	5,953,468	09/14/99	Finnila et al.			
	TC	5,561,305	10/01/96	Smith			
	TD	5,896,476	04/20/99	Wisseman et al.			
	TE	4,934,777	06/19/90	Jou et al.			
	TF	6,320,238 B1	11/20/01	Kizilyalli et al.			
	TG	6,393,167 B1	05/21/02	Davis et al.			
	TH	5,760,427	06/02/98	Onda			
	TI	6,411,756 B2	06/25/02	Sadot et al.			
	TJ	5,668,048	09/16/97	Kondo et al.			
	TK	5,852,687	12/22/98	Wickham			
	TL	5,122,852	06/16/92	Chan et al.			
	TM	5,173,835	12/22/92	Cornett et al.			
	TN	5,055,835	10/08/91	Sutton			
	TO	6,139,483	10/31/00	Seabaugh et al.			
	TP	5,283,462	02/01/94	Stengel			
	TQ	6,103,403	08/15/00	Grigorian et al.			

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BXB	UA	5,635,433	06/03/97	Sengupta			
	UB	5,427,988	06/27/95	Sengupta et al.			
	UC	6,297,842 B1	10/02/01	Koizumi et al.			
	UD	5,682,046	10/28/97	Takahashi et al.			
	UE	5,181,085	01/19/93	Moon et al.			
	UF	6,051,858	04/18/00	Uchida et al.			
	UG	6,013,553	01/11/00	Wallace et al.			
	UH	4,872,046	10/03/89	Morkoc et al.			
	UI	2002/0047123 A1	04/25/02	Ramdani et al.			
	UJ	5,995,528	11/30/99	Fukunaga et al.			
	UK	5,075,743	12/24/91	Behfar-Rad			
	UL	5,438,584	08/01/95	Paoli et al.			
	UM	4,503,540	03/05/85	Nakashima et al.			
	UN	5,373,166	12/13/94	Buchan et al.			
	UO	6,278,137 B1	08/21/01	Shimoyama et al.			
	UP	5,623,439	04/22/97	Gotoh et al.			
	UQ	4,981,714	01/01/91	Ohno et al.			
	UR	6,194,753 B1	02/27/01	Seon et al.			
	US	6,326,637 B1	12/04/01	Parkin et al.			
	UT						
	UU						
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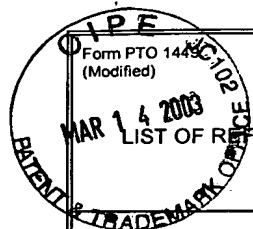
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	AAD	0 602 568	06/22/94	EP	X	
	AAE	0 607 435	07/27/94	EP	X	
	AAF	1 001 468	05/17/00	EP	X	
	AAG	0 514 018	11/19/92	EP	X	
	AAH	0 999 600	05/10/00	EP	X	
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	AAJ	5-291299	11/05/93	Japan w/English Abstract	X	
	AAK	11-238683	08/31/99	Japan	X	
	AAL	11-260835	09/24/99	Japan w/English Abstract	X	
	AAM	HEI 2-391	01/05/90	Japan w/English Abstract	X	
	AAN	5-48072	02/26/93	Japan w/English Abstract	X	
	AAO	52-88354	07/23/77	Japan w/English Abstract	X	
	AAP	54-134554	10/19/79	Japan w/English Abstract	X	
	AAQ	55-87424	07/02/80	Japan w/English Abstract	X	
	AAR	61-108187	05/26/86	Japan w/English Abstract	X	
	AAS	6-232126	08/19/94	Japan	X	
	AAT	6-291299	10/18/94	Japan w/English Abstract	X	
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	AAY	6-334168	12/02/94	Japan	X	
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	ABB	WO 97/45827	12/04/97	WIPO		
	ABC	WO 99/19546	04/22/99	WIPO		
	ABD	WO 00/33363	06/08/00	WIPO		
	ABE	WO 00/48239	08/17/00	WIPO		
	ABF	WO 99/14797	03/25/99	WIPO		
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	ABH	1 109 212	06/20/01	Europe		
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	ABL	WO 92/10875	06/25/92	WIPO		
	ABM	0 682 266	11/15/95	Europe		
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bmb	BAA	1 043 426	10/11/00	Europe		
	BAB	2000-068466	03/00	Japan (Abstract)		
	BAC	64-50575	02/27/89	Japan		
	BAD	WO 98/05807	01/12/98	WIPO		
	BAE	WO 94/03908	02/17/94	WIPO		
	BAF	WO 01/33585	05/10/01	WIPO		
	BAG	1-102435	04/20/89	Japan w/English Abstract		
	BAH	52-135684	11/12/77	Japan (English Abstract)		
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	BAJ	11135614	05/21/99	Japan (w/English Abstract)		
	BAK	64-52329	02/28/89	Japan (w/English Abstract)		
	BAL	10-256154	09/25/98	Japan (w/English Abstract)		
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	BAQ	0 875 922	11/04/98	Europe		
	BAR	61-63015	04/01/86	Japan w/English Abstract		
	BAS	11340542	12/10/99	Japan (English Abstract)		
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	BAX	0 964 453	12/15/99	Europe		
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	BAZ	9-67193	03/11/97	Japan w/English Abstract		
	BBA	9-82913	03/28/97	Japan w/English Abstract		
	BBB	0 309 270	03/29/89	Europe		
	BBC	EP 0 957 522	11/17/99	Europe		
	BBD	EP 0 810 666	12/03/97	Europe		
	BBE	1-179411	07/17/89	Japan w/English Abstract		
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	BBI	WO 01/59814 A2	08/16/01	WIPO		
	BBJ	WO 02/09160 A2	01/31/02	WIPO		
	BBK	WO 00/06812	02/10/00	WIPO		
	BBL	0 483 993	05/06/92	Europe		
	BBM	0 538 611	04/28/93	Europe		
	BBN	WO 01/59820 A1	08/16/01	WIPO		
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	CAC	WO 02/03113	01/10/02	WIPO		
	CAD	WO 02/03467	01/10/02	WIPO		
	CAE	0 630 057	12/21/94	EUROPE		
	CAF	61-36981	02/21/86	Japan w/English Abstract		
	CAG	WO 93/07647	04/15/93	WIPO		
	CAH	2002-9366	01/11/02	Japan w/English Abstract		
	CAI	EP 0 881 669	12/02/98	Europe		
	CAJ	WO 02/03480	01/10/02	WIPO		
	CAK	WO 02/50879	06/27/02	WIPO		
	CAL	EP 0 777 379	06/04/97	Europe		
	CAM	WO 01/04943 A1	01/18/01	WIPO		xx
	CAN	WO 02/47127 A2	06/13/02	WIPO		
	CAO	JP 58-075868	05/07/83	Japan w/English Abstract		
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	CAQ	EP 0 711 853	05/15/96	Europe		
	CAR	WO 98/20606	05/14/98	WIPO		
	CAS	EP 1 043 765	10/11/00	Europe		
	CAT	0 300 499	01/25/89	Europe		
	CAU	EP 1 085 319	03/21/01	Europe		
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	CAW	2000-351692	12/19/00	Japan w/English Abstract		
	CAX	03-188619	08/16/91	Japan (English Abstract only)		
	CAY	63-289812	11/28/88	Japan (English Abstract only)		
	CAZ	EP 0 884 767	12/16/98	Europe		
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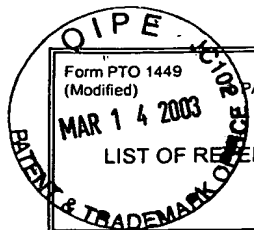
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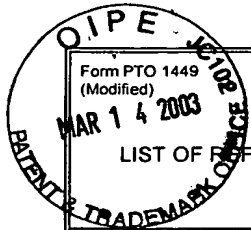
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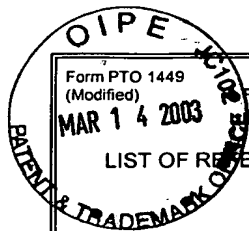
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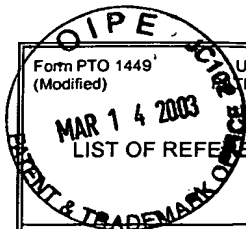
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LIST OF REFERENCES CITED BY APPLICANT		APPLICANT Ravindranath DROOPAD, et al.			
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